# **MOSFET** - Power, Single, N-Channel, SO-8 FL 30 V, 47 A

### **Features**

- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## **Applications**

- CPU Power Delivery
- DC-DC Converters

## **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise stated)

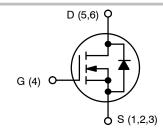
Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			$V_{DSS}$	30	V
Gate-to-Source Vol	te-to-Source Voltage				V
Continuous Drain		T <sub>A</sub> = 25°C	I <sub>D</sub>	15	Α
Current R <sub>θJA</sub> (Note 1)		T <sub>A</sub> = 100°C		9.4	
Power Dissipation $R_{\theta JA}$ (Note 1)		T <sub>A</sub> = 25°C	P <sub>D</sub>	2.56	W
Continuous Drain		T <sub>A</sub> = 25°C	I <sub>D</sub>	25	Α
Current R <sub>θJA</sub> ≤ 10 s (Note 1)		T <sub>A</sub> = 100°C		16	
Power Dissipation $R_{\theta JA} \le 10 \text{ s}$ (Note 1)	Steady	T <sub>A</sub> = 25°C	P <sub>D</sub>	7.2	W
Continuous Drain	State	T <sub>A</sub> = 25°C	I <sub>D</sub>	9.0	Α
Current R <sub>θJA</sub> (Note 2)		T <sub>A</sub> = 100°C		5.7	
Power Dissipation $R_{\theta JA}$ (Note 2)	1	T <sub>A</sub> = 25°C	P <sub>D</sub>	0.91	W
Continuous Drain		T <sub>C</sub> = 25°C	Ι <sub>D</sub>	47	Α
Current R <sub>θJC</sub> (Note 1)		T <sub>C</sub> =100°C		30	
Power Dissipation $R_{\theta JC}$ (Note 1)		T <sub>C</sub> = 25°C	P <sub>D</sub>	25.5	W
Pulsed Drain Current	$T_A = 25^{\circ}$	<sup>o</sup> C, t <sub>p</sub> = 10 μs	I <sub>DM</sub>	140	Α
Current Limited by P	Current Limited by Package T <sub>A</sub> = 25°C		I <sub>Dmax</sub>	100	Α
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C
Source Current (Body Diode)			I <sub>S</sub>	23	Α
Drain to Source DV/DT			dV/d <sub>t</sub>	7.5	V/ns



## ON Semiconductor®

#### http://onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX	
30 V	6.2 m $\Omega$ @ 10 V	47 A	
	9.0 mΩ @ 4.5 V	7/7	



**N-CHANNEL MOSFET** 



## **SO-8 FLAT LEAD** CASE 488AA STYLE 1

**DIAGRAM** S 4941N S **AYWZZ** S G

**MARKING** 

Α = Assembly Location Υ = Year = Work Week W ZZ = Lot Traceability

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NTMFS4941NT1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NTMFS4941NT3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit
Single Pulse Drain-to-Source Avalanche Energy $T_J$ = 25°C, $V_{DD}$ = 50 V, $V_{GS}$ = 10 V, $I_L$ = 29 $A_{pk}$ , $L$ = 0.1 mH, $R_G$ = 25 $\Omega$	E <sub>AS</sub>	42	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- 2. Surface-mounted on FR4 board using the minimum recommended pad size.

#### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{ heta JC}$	4.9	
Junction-to-Ambient - Steady State (Note 3)	$R_{\theta JA}$	48.8	0000
Junction-to-Ambient - Steady State (Note 4)	$R_{\theta JA}$	137	°C/W
Junction-to-Ambient – (t ≤ 10 s) (Note 3)	$R_{\theta JA}$	17.5	

- 3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- 4. Surface-mounted on FR4 board using the minimum recommended pad size.

## **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30			V
Drain-to-Source Breakdown Voltage (transient)	V <sub>(BR)DSSt</sub>	VGS = 0 V, I <sub>D(aval)</sub> = 12 A, T <sub>case</sub> = 25°C, t <sub>transient</sub> = 100 ns		34			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> / T <sub>J</sub>				15		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V,				1.0	
		V <sub>DS</sub> = 24 V	T <sub>J</sub> = 125°C			10	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$				±100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 250 \mu A$		1.2	1.67	2.2	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				4.0		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A		4.7	6.2	
			I <sub>D</sub> = 15 A		4.7		mΩ
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 30 A		7.1	9.0	] 11152
			I <sub>D</sub> = 15 A		7.1		
Forward Transconductance	9FS	$V_{DS} = 1.5 \text{ V}, I_{D}$	<sub>)</sub> = 15 A		32		S
CHARGES, CAPACITANCES & GATE RESIS	TANCE						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 15 V			1650		
Output Capacitance	C <sub>OSS</sub>				570		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>	1			17		
Capacitance Ratio	C <sub>RSS</sub> / C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 15 V, f = 1 MHz			0.010	0.021	

- 5. Pulse Test: pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2%.
- 6. Switching characteristics are independent of operating junction temperatures.

## **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condi	tion	Min	Тур	Max	Unit
CHARGES, CAPACITANCES & GATE	RESISTANCE					•	-
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5 \text{ V}, V_{DS} = 15 \text{ V}; I_D = 30 \text{ A}$ $V_{GS} = 10 \text{ V}, V_{DS} = 15 \text{ V}; I_D = 30 \text{ A}$			11.3		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>				2.9		
Gate-to-Source Charge	Q <sub>GS</sub>				5.7		
Gate-to-Drain Charge	$Q_{GD}$				1.64		
Total Gate Charge	Q <sub>G(TOT)</sub>				25.5		nC
SWITCHING CHARACTERISTICS (No	ote 6)						
Turn-On Delay Time	t <sub>d(ON)</sub>	$V_{GS}$ = 4.5 V, $V_{DS}$ = 15 V, $I_{D}$ = 15 A, $R_{G}$ = 3.0 $\Omega$			11.6		- ns
Rise Time	t <sub>r</sub>				22		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				20		
Fall Time	t <sub>f</sub>				2.7		
Turn-On Delay Time	t <sub>d(ON)</sub>	$V_{GS}$ = 10 V, $V_{DS}$ = 15 V, $I_{D}$ = 15 A, $R_{G}$ = 3.0 $\Omega$			9.0		ns
Rise Time	t <sub>r</sub>				21.8		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				23.8		
Fall Time	t <sub>f</sub>				2.8		
DRAIN-SOURCE DIODE CHARACTE	RISTICS						
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V,	T <sub>J</sub> = 25°C		0.91	1.1	V
		I <sub>S</sub> = 30 A	T <sub>J</sub> = 125°C		0.81		ľ
Reverse Recovery Time	t <sub>RR</sub>				32		
Charge Time	t <sub>a</sub>	V <sub>GS</sub> = 0 V, dIS/dt =	= 100 A/μs,		16.6		ns
Discharge Time	t <sub>b</sub>	l <sub>S</sub> = 30 A			15.4		
Reverse Recovery Charge	Q <sub>RR</sub>				25		nC
PACKAGE PARASITIC VALUES							
Source Inductance	L <sub>S</sub>				0.93		nH
Drain Inductance	L <sub>D</sub>	T 050	^		0.005		nH
Gate Inductance	L <sub>G</sub>	T <sub>A</sub> = 25°C			1.84		nH
Gate Resistance	R <sub>G</sub>				1.1	2.0	Ω

<sup>5.</sup> Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

#### **TYPICAL CHARACTERISTICS**

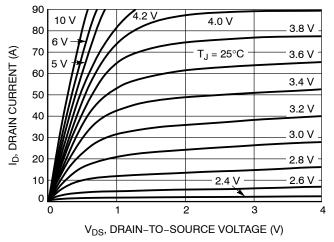


Figure 1. On-Region Characteristics

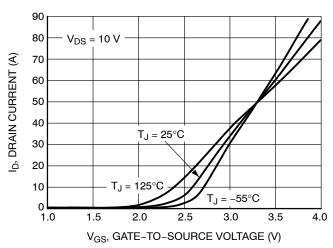


Figure 2. Transfer Characteristics

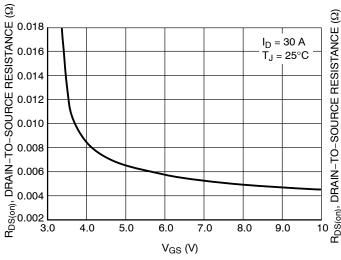


Figure 3. On-Resistance vs. V<sub>GS</sub>

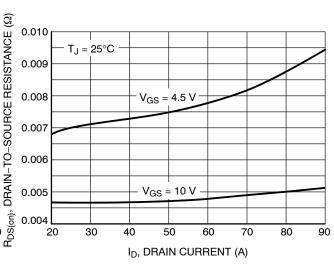


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

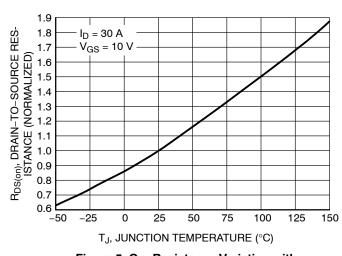


Figure 5. On–Resistance Variation with Temperature

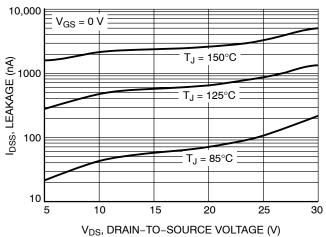


Figure 6. Drain-to-Source Leakage Current vs. Voltage

### **TYPICAL CHARACTERISTICS**

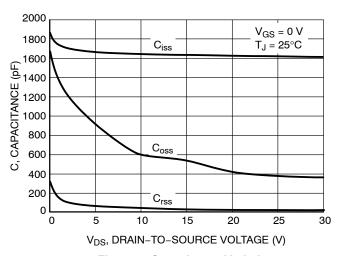


Figure 7. Capacitance Variation

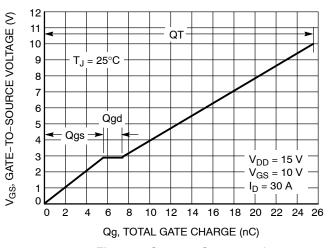


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

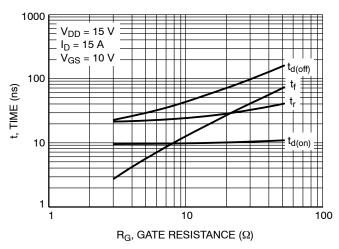


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

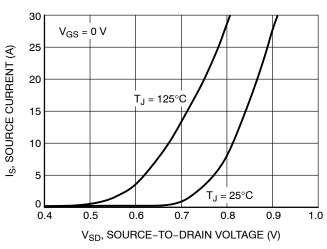


Figure 10. Diode Forward Voltage vs. Current

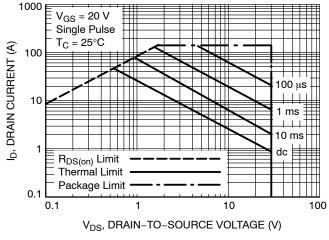


Figure 11. Maximum Rated Forward Biased Safe Operating Area

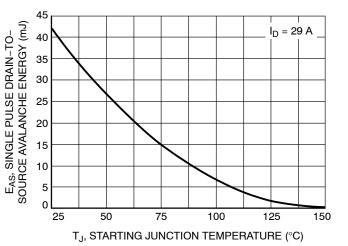


Figure 12. Maximum Avalanche Energy vs.
Starting Junction Temperature

## **TYPICAL CHARACTERISTICS**

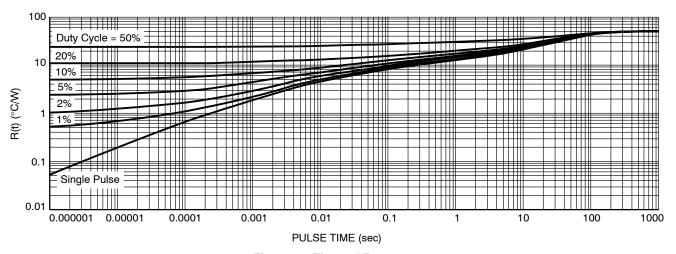


Figure 13. Thermal Response

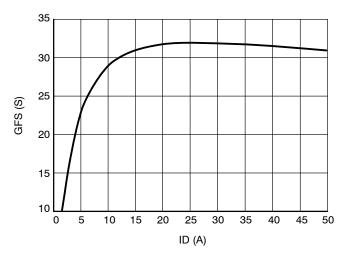


Figure 14. GFS vs. ID



0.10

0.10

SIDE VIEW

DFN5 5x6, 1.27P (SO-8FL) CASE 488AA ISSUE N

**DATE 25 JUN 2018** 

#### NOTES:

BURRS

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETER. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE

	MILLIMETERS					
DIM	MIN	NOM	MAX			
Α	0.90	1.00	1.10			
A1	0.00		0.05			
b	0.33	0.41	0.51			
С	0.23	0.28	0.33			
D	5.00	5.15	5.30			
D1	4.70	4.90	5.10			
D2	3.80	4.00	4.20			
E	6.00	6.15	6.30			
E1	5.70	5.90	6.10			
E2	3.45	3.65	3.85			
е		1.27 BSC	;			
G	0.51	0.575	0.71			
K	1.20	1.35	1.50			
L	0.51	0.575	0.71			
L1	0.125 REF					
М	3.00	3.40	3.80			
A	0 0		12 °			

#### **GENERIC** MARKING DIAGRAM\*



XXXXXX = Specific Device Code

= Assembly Location Α

Υ = Year W = Work Week ZZ = Lot Traceability

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.





**DETAIL A** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)		PAGE 1 OF 1	

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